

# Silizium-PIN-Fotodiode mit sehr kurzer Schaltzeit

## Silicon PIN Photodiode with Very Short Switching Time

### SFH 213 SFH 213 FA



SFH 213



SFH 213 FA

#### Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 400 nm bis 1100 nm (SFH 213) und bei 880 nm (SFH 213 FA)
- Kurze Schaltzeit (typ. 5 ns)
- 5 mm-Plastikbauform im LED-Gehäuse
- Auch gegurtet lieferbar

#### Features

- Especially suitable for applications from 400 nm to 1100 nm (SFH 213) and of 880 nm (SFH 213 FA)
- Short switching time (typ. 5 ns)
- 5 mm LED plastic package
- Also available on tape and reel

#### Anwendungen

- Industrieelektronik
- „Messen/Steuern/Regeln“
- Schnelle Lichtschranken für Gleich- und Wechsellichtbetrieb
- LWL

#### Applications

- Industrial electronics
- For control and drive circuits
- Photointerrupters
- Fiber optic transmission systems

Typ Type	Bestellnummer Ordering Code
SFH 213	Q62702-P930
SFH 213 FA	Q62702-P1671

**Grenzwerte****Maximum Ratings**

<b>Bezeichnung Parameter</b>	<b>Symbol Symbol</b>	<b>Wert Value</b>	<b>Einheit Unit</b>
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{\text{op}}; T_{\text{stg}}$	- 40 ... + 100	°C
Löttemperatur (Lötstelle 2 mm vom Gehäuse entfernt bei Lötzeit $t \leq 3$ s) Soldering temperature in 2 mm distance from case bottom ( $t \leq 3$ s)	$T_S$	300	°C
Sperrspannung Reverse voltage	$V_R$	50	V
Verlustleistung Total power dissipation	$P_{\text{tot}}$	100	mW

**Kennwerte ( $T_A = 25$  °C)****Characteristics**

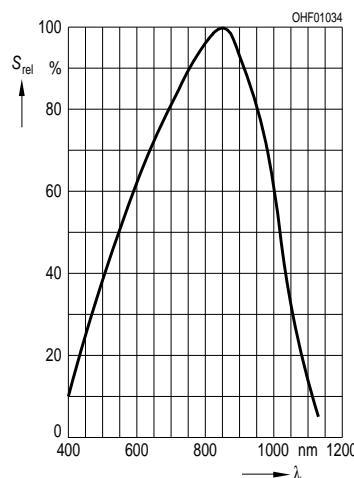
<b>Bezeichnung Parameter</b>	<b>Symbol Symbol</b>	<b>Wert Value</b>		<b>Einheit Unit</b>
		<b>SFH 213</b>	<b>SFH 213 FA</b>	
Fotostrom Photocurrent $V_R = 5$ V, Normlicht/standard light A, $T = 2856$ K, $E_V = 1000$ lx $V_R = 5$ V, $\lambda = 870$ nm, $E_e = 1$ mW/cm <sup>2</sup>	$I_P$	135 ( $\geq 100$ )	-	μA
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S \text{ max}}$	850	900	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von $S_{\text{max}}$ Spectral range of sensitivity $S = 10\%$ of $S_{\text{max}}$	$\lambda$	400 ... 1100	750 ... 1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	1	1	mm <sup>2</sup>
Abmessung der bestrahlungsempfindlichen Fläche Dimensions of radiant sensitive area	$L \times B$ $L \times W$	1 × 1	1 × 1	mm × mm
Abstand Chipoberfläche zu Gehäuseoberfläche Distance chip front to case surface	H	5.1 ... 5.7	5.1 ... 5.7	mm
Halbwinkel Half angle	φ	± 10	± 10	Grad deg.

Kennwerte ( $T_A = 25^\circ\text{C}$ )

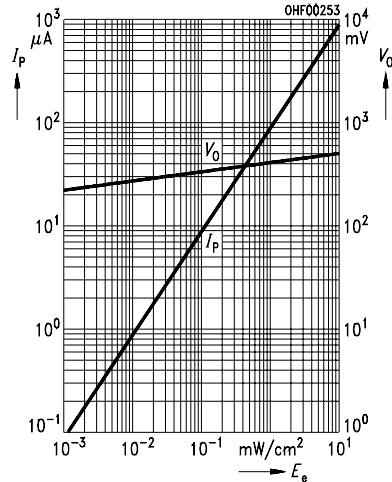
Characteristics (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value		Einheit Unit
		SFH 213	SFH 213 FA	
Dunkelstrom, $V_R = 20\text{ V}$ Dark current	$I_R$	1 ( $\leq 5$ )	1 ( $\leq 5$ )	nA
Spektrale Fotoempfindlichkeit, $\lambda = 870\text{ nm}$ Spectral sensitivity	$S_\lambda$	0.62	0.59	A/W
Quantenausbeute, $\lambda = 870\text{ nm}$ Quantum yield	$\eta$	0.89	0.86	Electrons Photon
Leerlaufspannung Open-circuit voltage $E_v = 1000\text{ lx}$ , Normlicht/standard light A, $T = 2856\text{ K}$ $E_e = 0.5\text{ mW/cm}^2$ , $\lambda = 870\text{ nm}$	$V_O$	430 ( $\geq 350$ )	–	mV
	$V_O$	–	380 ( $\geq 300$ )	mV
Kurzschlußstrom Short-circuit current $E_v = 1000\text{ lx}$ , Normlicht/standard light A, $T = 2856\text{ K}$ $E_e = 0.5\text{ mW/cm}^2$ , $\lambda = 870\text{ nm}$	$I_{SC}$	125	–	$\mu\text{A}$
	$I_{SC}$	–	42	$\mu\text{A}$
Anstiegs- und Abfallzeit des Fotostromes Rise and fall time of the photocurrent $R_L = 50\text{ }\Omega$ ; $V_R = 20\text{ V}$ ; $\lambda = 850\text{ nm}$ ; $I_p = 800\text{ }\mu\text{A}$	$t_r, t_f$	5	5	ns
Durchlaßspannung, $I_F = 80\text{ mA}$ , $E = 0$ Forward voltage	$V_F$	1.3	1.3	V
Kapazität, $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$ Capacitance	$C_0$	11	11	pF
Temperaturkoeffizient von $V_O$ Temperature coefficient of $V_O$	$TC_V$	– 2.6	– 2.6	mV/K
Temperaturkoeffizient von $I_{SC}$ Temperature coefficient of $I_{SC}$ Normlicht/standard light A $\lambda = 870\text{ nm}$	$TC_I$	0.18 –	– 0.2	%/K
Rauschäquivalente Strahlungsleistung Noise equivalent power $V_R = 10\text{ V}$ , $\lambda = 870\text{ nm}$	$NEP$	$2.9 \times 10^{-14}$	$2.9 \times 10^{-14}$	$\frac{\text{W}}{\sqrt{\text{Hz}}}$
Nachweisgrenze, $V_R = 20\text{ V}$ , $\lambda = 870\text{ nm}$ Detection limit	$D^*$	$3.5 \times 10^{12}$	$3.5 \times 10^{12}$	$\frac{\text{cm} \times \sqrt{\text{Hz}}}{\text{W}}$

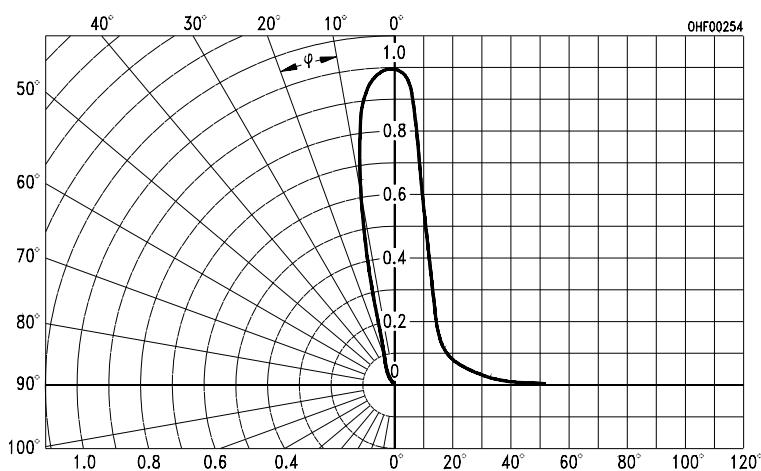
**Relative Spectral Sensitivity**  
SFH 213,  $S_{\text{rel}} = f(\lambda)$



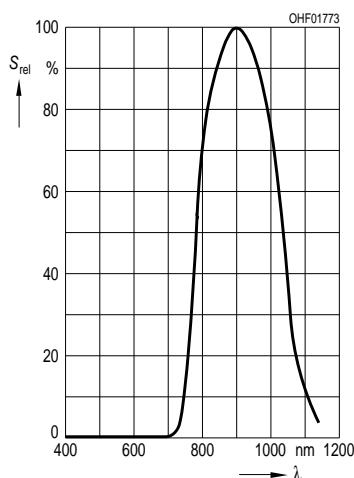
**Photocurrent  $I_P = f(E_e)$ ,  $V_R = 5$  V**  
**Open-Circuit Voltage  $V_O = f(E_e)$**   
SFH 213 FA



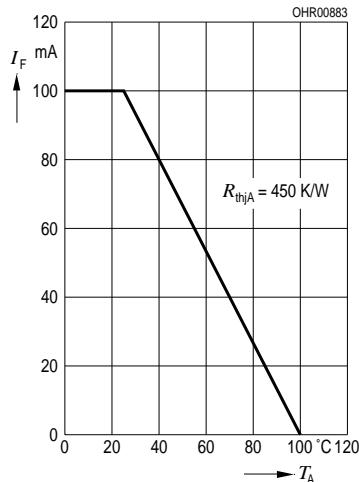
**Directional Characteristics**  
 $S_{\text{rel}} = f(\phi)$



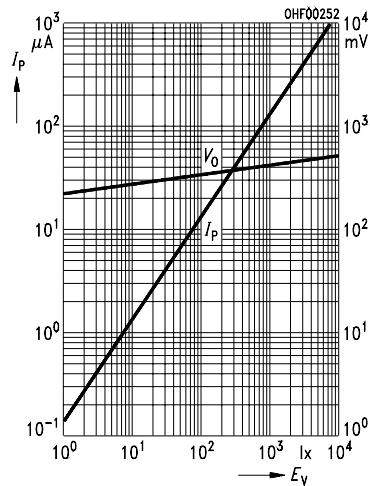
**Relative Spectral Sensitivity**  
SFH 213 FA,  $S_{\text{rel}} = f(\lambda)$



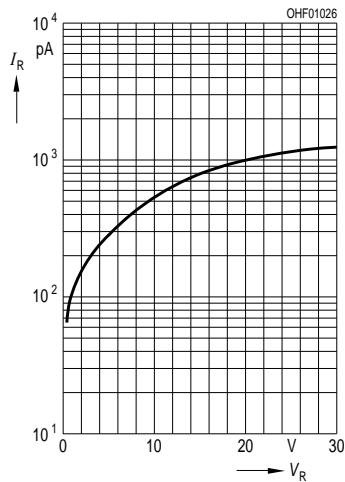
**Total Power Dissipation**  
 $P_{\text{tot}} = f(T_A)$



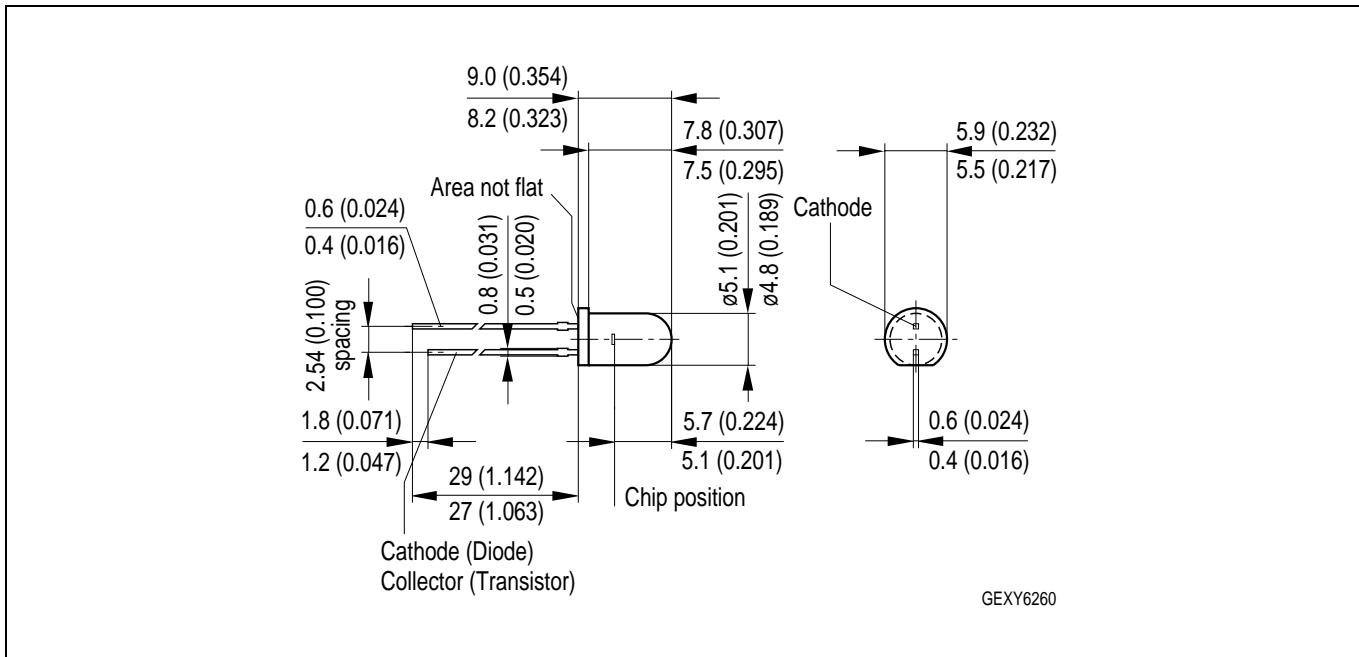
**Photocurrent  $I_P = f(E_v)$ ,  $V_R = 5$  V**  
**Open-Circuit Voltage  $V_O = f(E_v)$**   
SFH 213



**Dark Current**  
 $I_R = f(V_R)$ ,  $E = 0$



## Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

Published by OSRAM Opto Semiconductors GmbH & Co. OHG  
Wernerwerkstrasse 2, D-93049 Regensburg

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### Attention please!

The information describes the type of component and shall not be considered as assured characteristics.  
Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances. For information on the types in question please contact our Sales Organization.

### Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

**Components used in life-support devices or systems must be expressly authorized for such purpose!** Critical components<sup>1</sup>, may only be used in life-support devices or systems<sup>2</sup> with the express written approval of OSRAM OS.

<sup>1</sup> A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

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